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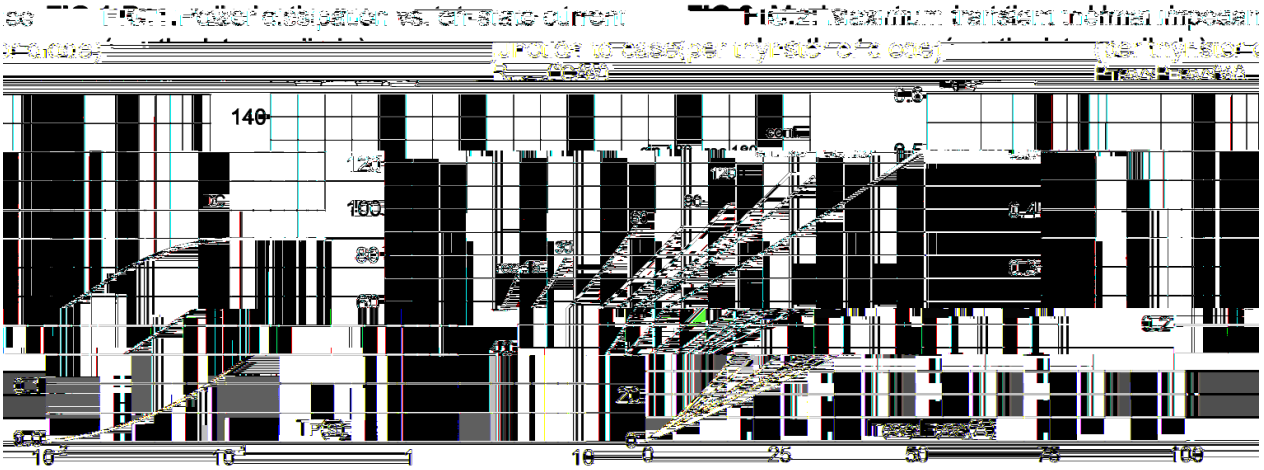


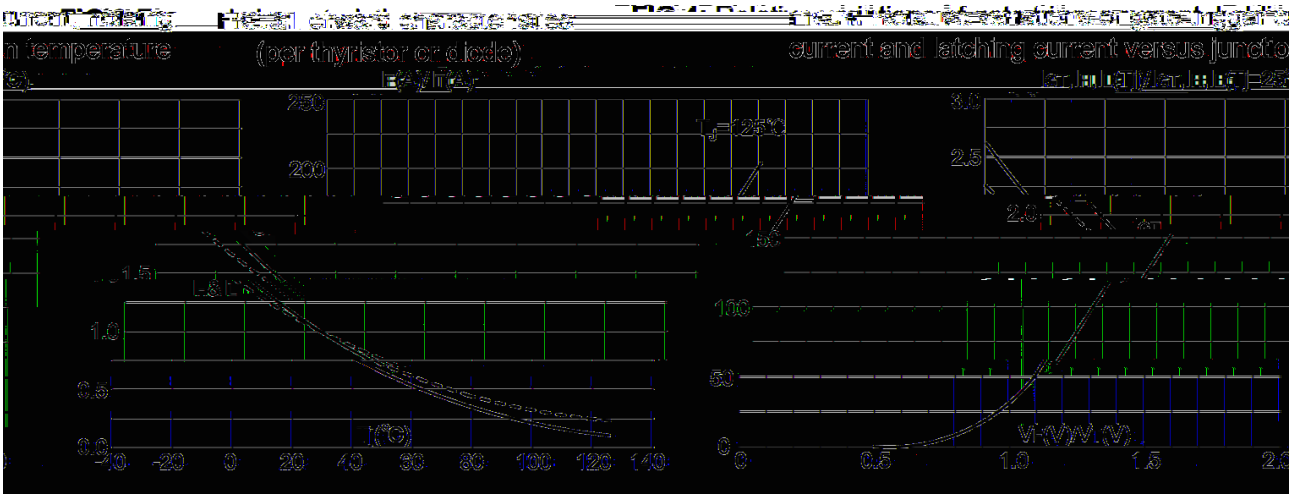


FIG.5 Gate trigger characteristics

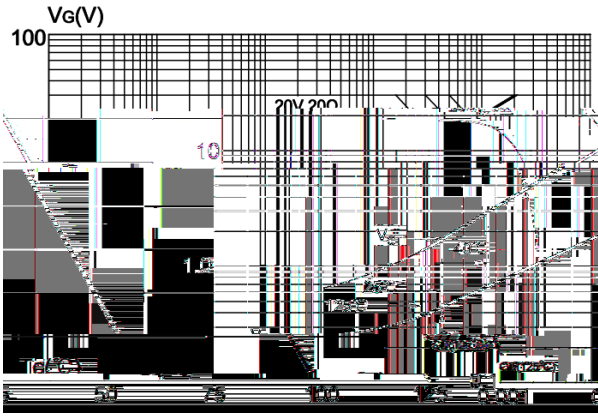
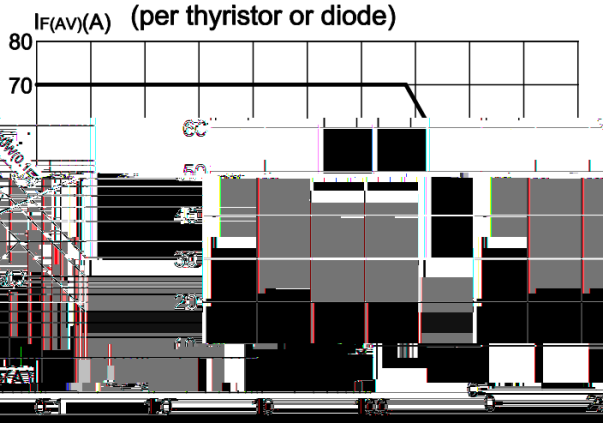
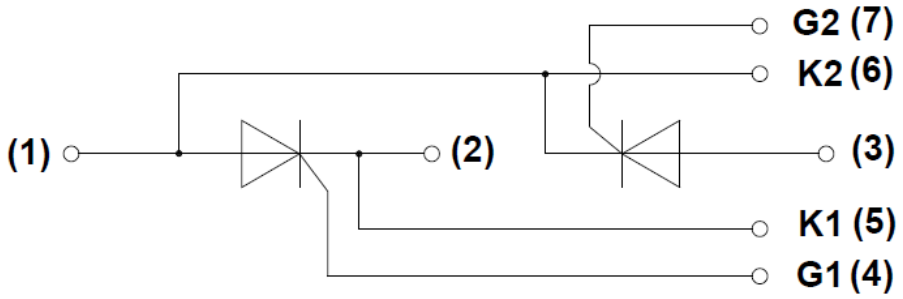
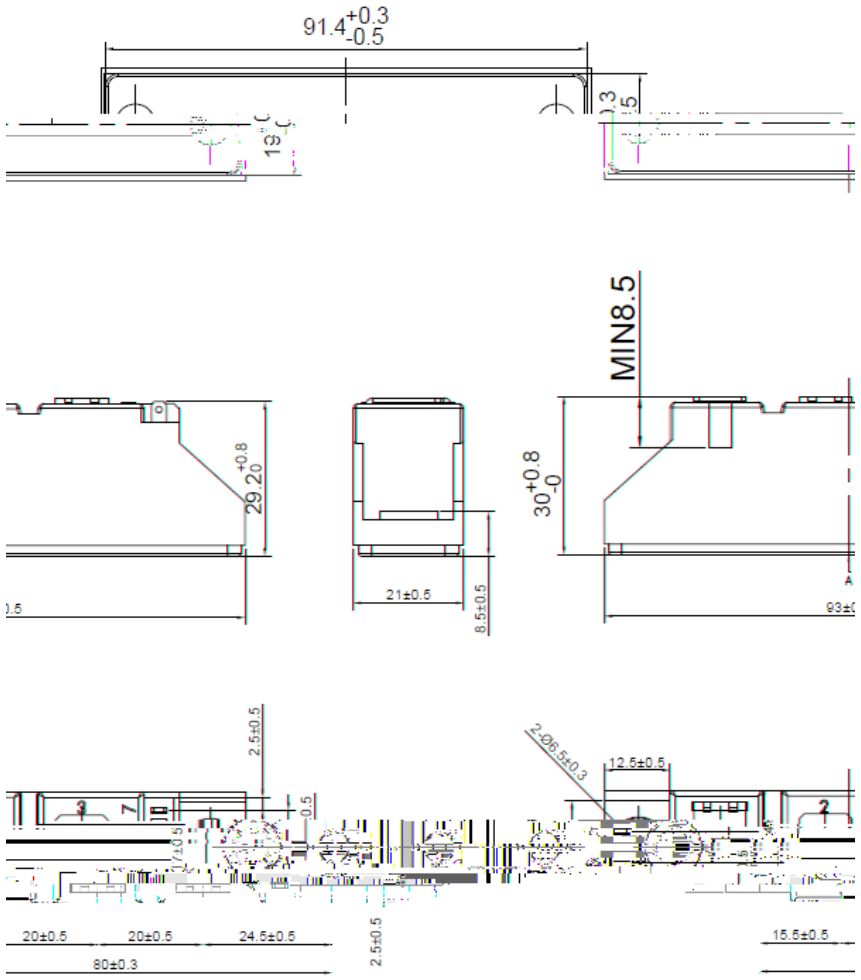


FIG.6: Forward current vs. case temperature (per thyristor or diode)




G2 (7)
K2 (6)
(1)
(2)
(3)
K1 (5)
G1 (4)


91.4+0.3 -0.5
MIN8.5
29.2+0.8 0
30+0.8 -0
21±0.5
8.5±0.5
2.5±0.5
2-Ø6.5±0.3
12.5±0.5
20±0.5
20±0.5
24.5±0.5
80±0.3
2.5±0.5
15.5±0.5